DMG204B0

Silicon NPN epitaxial planar type (Tr1) Silicon PNP epitaxial planar type (Tr2)

For low frequency amplification

■ Features

- \bullet High forward current transfer ratio h_{FE} with excellent linearity
- Low collector-emitter saturation voltage V_{CE(sat)}
- Halogen-free / RoHS compliant
 (EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

■ Marking Symbol: C4

■ Basic Part Number

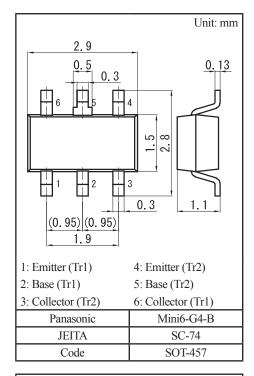
DSC2001 + DSA2401 (Individual)

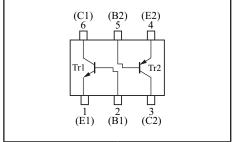
Packaging

DMG204B00R Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25$ °C

	Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	V _{CBO}	60	V
	Collector-emitter voltage (Base open)	V _{CEO}	50	V
	Emitter-base voltage (Collector open)	V _{EBO}	7	V
	Collector current	I_{C}	100	mA
	Peak collector current	I _{CP}	200	mA
Tr2	Collector-base voltage (Emitter open)	V _{CBO}	-15	V
	Collector-emitter voltage (Base open)	V _{CEO}	-10	V
	Emitter-base voltage (Collector open)	V _{EBO}	-7	V
	Collector current	I_{C}	-0.5	A
	Peak collector current	I_{CP}	-1	A
Overall	Total power dissipation	P _T	300	mW
	Junction temperature	T_j	150	°C
	Operating ambient temperature	T _{opr}	-40 to +85	°C
	Storage temperature	T _{stg}	-55 to +150	°C





■ Electrical Characteristics $T_a = 25$ °C±3°C

• Tr

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10 \mu A, I_E = 0$	60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 2 \text{ mA}, I_{\rm B} = 0$	50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu A, I_C = 0$	7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 20 \text{ V}, I_{E} = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 10 \text{ V}, I_{B} = 0$			100	μΑ
Forward current transfer ratio	h_{FE}	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	210		460	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$		0.13	0.3	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		1.5		pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

• Tr2

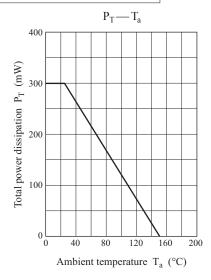
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = -10 \mu{\rm A}, I_{\rm E} = 0$	-15			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -1 \text{ mA}, I_{\rm B} = 0$	-10			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -10 \text{ V}, I_E = 0$			-100	nA
F	h _{FE1}	$V_{CE} = -2 \text{ V}, I_{C} = -0.5 \text{ A}$	130		350	_
Forward current transfer ratio *1	h _{FE2}	$V_{CE} = -2 \text{ V}, I_{C} = -1 \text{ A}$	60			
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_C = -0.4 \text{ A}, I_B = -8 \text{ mA}$		-0.15	-0.30	V
Base-emitter saturation voltage *1	V _{BE(sat)}	$II_C = -0.4 \text{ A}, I_B = -8 \text{ mA}$		- 0.8	-1.2	V
Transition frequency	f_T	$V_{CE} = -10 \text{ V}, I_{C} = -50 \text{ mA}$		250		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		18		pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

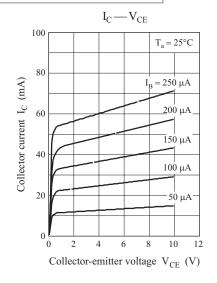
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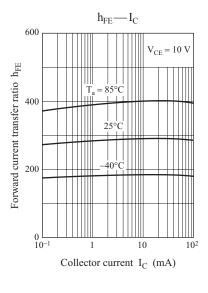
^{2. *1:} Pulse measurement

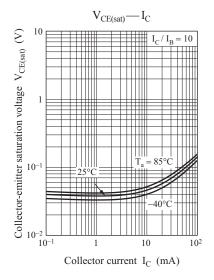
Common characteristics chart

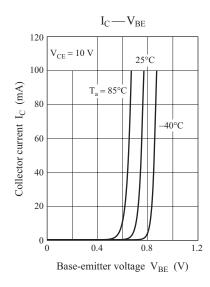


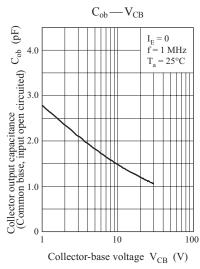
Characteristics charts of Tr1

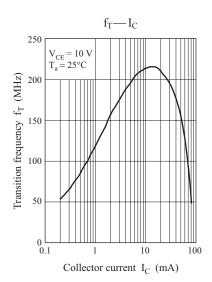




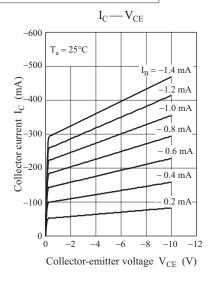


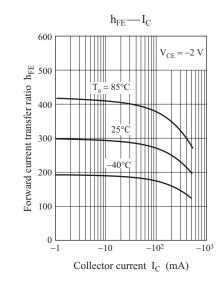


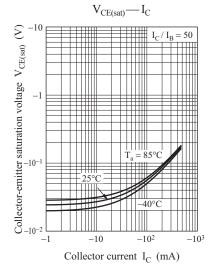


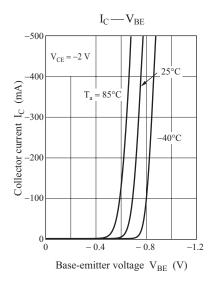


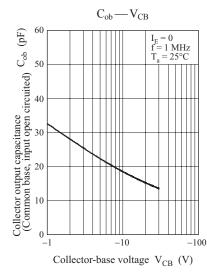
Characteristics charts of Tr2

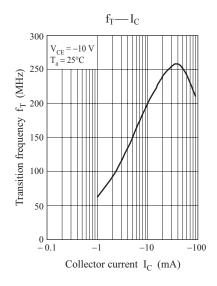


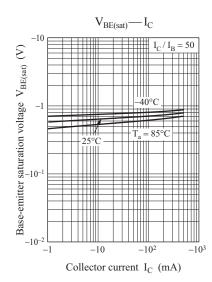








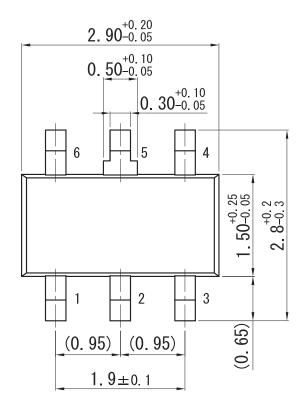


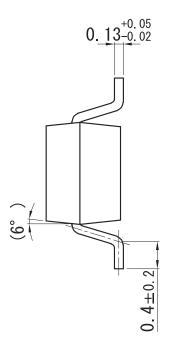


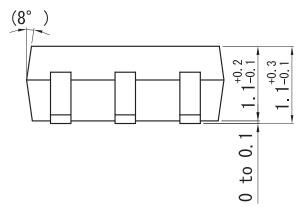
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Mini6-G4-B

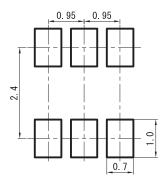
Unit: mm







■ Land Pattern (Reference) (Unit: mm)



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